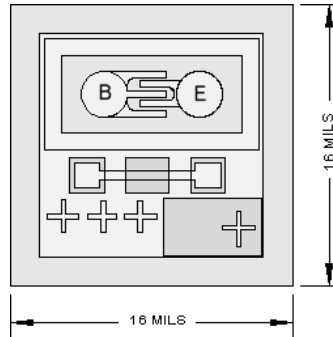


Chip Type 2C2857
Geometry 0011
Polarity NPN

Generic Packaged Part:
2N2857



[Request Quotation](#)

Chip type **2C2857** by Semicoa Semiconductors provides performance similar to these devices.

Product Summary:

APPLICATIONS: Designed for use in high-gain, low noise amplifier, oscillator, mixer and UHF converters.

Part Numbers:

2N2857, 2N2857UB, SD2857, SD2857F, SQ2857, SQ2857F

Features: $f_t = 1.2 \text{ GHz (typ) at } 5 \text{ mA/6V}$

| Mechanical Specifications | | |
|---------------------------|-------------------|---------------------|
| Metallization | Top | Al - 15 kÅ min. |
| | Backside | Au - 6.5 kÅ nom. |
| Bonding Pad Size | Emitter | 2.3 mils x 2.3 mils |
| | Base | 2.3 mils x 2.3 mils |
| Die Thickness | 8 mils nominal | |
| Chip Area | 16 mils x 16 mils | |
| Top Surface | Silox Passivated | |

| Electrical Characteristics | | | | |
|----------------------------|---|-----|------|------------------|
| $T_A = 25^\circ\text{C}$ | | | | |
| Parameter | Test conditions | Min | Max | Unit |
| BV_{CEO} | $I_C = 3.0 \text{ mA}$ | 15 | --- | V dc |
| BV_{CBO} | $I_C = 1.0 \mu\text{A}$ | 30 | --- | V dc |
| BV_{EBO} | $I_E = 10 \mu\text{A}$ | 2.5 | --- | V dc |
| I_{CBO} | $V_{CB} = 15 \text{ V}$ | --- | 0.01 | $\mu\text{A dc}$ |
| h_{FE} | $I_C = 3.0 \text{ mA dc}, V_{CE} = 1.0 \text{ V}$ | 30 | 150 | --- |

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width of less than 300 μs , duty cycle less than 2%.